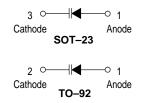
## **Silicon Tuning Diodes**

These devices are designed in the popular PLASTIC PACKAGE for high volume requirements of FM Radio and TV tuning and AFC, general frequency control and tuning applications. They provide solid–state reliability in replacement of mechanical tuning methods. Also available in Surface Mount Package up to 33pF.

- High Q
- · Controlled and Uniform Tuning Ratio
- Standard Capacitance Tolerance 10%
- · Complete Typical Design Curves



### **MAXIMUM RATINGS**

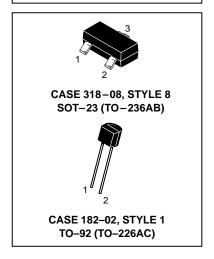
| Rating  | Symbol           | MV21xx      | MMBV21xxLT1 | Unit        |
|---|------------------|-------------|-------------|-------------|
| Reverse Voltage   | VR               |             | 30          |             |
| Forward Current   | lF               |             | mAdc        |             |
| Forward Power Dissipation<br>@ T <sub>A</sub> = 25°C<br>Derate above 25°C | PD               | 280<br>2.8  | 225<br>1.8  | mW<br>mW/°C |
| Junction Temperature  | TJ               | +150        |             | °C          |
| Storage Temperature Range   | T <sub>stg</sub> | -55 to +150 |             | °C          |

### **DEVICE MARKING**

| MMBV2101LT1 = M4G<br>MMBV2103LT1 = 4H | MMBV2107LT1 = 4W<br>MMBV2108LT1 = 4X |
|---------------------------------------|--------------------------------------|
| MMBV2105LT1 = 4U                      | MMBV2109LT1 = 4J                     |

MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115

6.8-100 pF 30 VOLTS VOLTAGE VARIABLE CAPACITANCE DIODES



### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol         | Min | Тур | Max | Unit   |
|---|----------------|-----|-----|-----|--------|
| Reverse Breakdown Voltage ( $I_R = 10 \mu Adc$ )                                  | V(BR)R         | 30  |     |     | Vdc    |
| Reverse Voltage Leakage Current (V <sub>R</sub> = 25 Vdc, T <sub>A</sub> = 25°C)  | I <sub>R</sub> | 1   | _   | 0.1 | μAdc   |
| Diode Capacitance Temperature Coefficient (V <sub>R</sub> = 4.0 Vdc, f = 1.0 MHz) | TCC            | 1   | 280 | ı   | ppm/°C |

Thermal Clad is a trademark of the Bergquist Company

### MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115

|                    | C <sub>T</sub> , Diode Capacitance<br>V <sub>R</sub> = 4.0 Vdc, f = 1.0 MHz<br>pF |     | Q, Figure of Merit<br>V <sub>R</sub> = 4.0 Vdc,<br>f = 50 MHz | 0 Vdc, C <sub>2</sub> /C <sub>30</sub> |     | io  |     |
|--------------------|---|-----|---|--|-----|-----|-----|
| Device             | Min   | Nom | Max   | Тур                                    | Min | Тур | Max |
| MMBV2101LT1/MV2101 | 6.1   | 6.8 | 7.5   | 450                                    | 2.5 | 2.7 | 3.2 |
| MMBV2103LT1        | 9.0   | 10  | 11  | 400                                    | 2.5 | 2.9 | 3.2 |
| MV2104             | 10.8  | 12  | 13.2  | 400                                    | 2.5 | 2.9 | 3.2 |
| MMBV2105LT1/MV2105 | 13.5  | 15  | 16.5  | 400                                    | 2.5 | 2.9 | 3.2 |
| MMBV2107LT1        | 19.8  | 22  | 24.2  | 350                                    | 2.5 | 2.9 | 3.2 |
| MMBV2108LT1/MV2108 | 24.3  | 27  | 29.7  | 300                                    | 2.5 | 3.0 | 3.2 |
| MMBV2109LT1/MV2109 | 29.7  | 33  | 36.3  | 200                                    | 2.5 | 3.0 | 3.2 |
| MV2111             | 42.3  | 47  | 51.7  | 150                                    | 2.5 | 3.0 | 3.2 |
| MV2115             | 90  | 100 | 110   | 100                                    | 2.6 | 3.0 | 3.3 |

MMBV2101LT1, MMBV2103LT1, MMBV2105LT1, MMBV2107LT1 thru MMBV2109LT1, are also available in bulk. Use the device title and drop the "T1" suffix when ordering any of these devices in bulk.

### PARAMETER TEST METHODS

### 1. C<sub>T</sub>, DIODE CAPACITANCE

 $(C_T = C_C + C_J)$ .  $C_T$  is measured at 1.0 MHz using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

### 2. TR, TUNING RATIO

TR is the ratio of  $C_T$  measured at 2.0 Vdc divided by  $C_T$  measured at 30 Vdc.

### 3. Q, FIGURE OF MERIT

Q is calculated by taking the G and C readings of an admittance bridge at the specified frequency and substituting in the following equations:

$$Q\,=\,\frac{2\pi fC}{G}$$

(Boonton Electronics Model 33AS8 or equivalent). Use Lead Length  $\approx$  1/16".

## 4. TC<sub>C</sub>, DIODE CAPACITANCE TEMPERATURE COEFFICIENT

TC<sub>C</sub> is guaranteed by comparing C<sub>T</sub> at  $V_R = 4.0$  Vdc, f = 1.0 MHz,  $T_A = -65^{\circ}$ C with C<sub>T</sub> at  $V_R = 4.0$  Vdc, f = 1.0 MHz,  $T_A = +85^{\circ}$ C in the following equation, which defines TC<sub>C</sub>:

$$\mathsf{TC}_{\mathsf{C}} = \left| \frac{\mathsf{C}_{\mathsf{T}}(+\ 85^{\circ}\mathsf{C}) - \mathsf{C}_{\mathsf{T}}(-65^{\circ}\mathsf{C})}{85 + 65} \right| \cdot \frac{10^{6}}{\mathsf{C}_{\mathsf{T}}(25^{\circ}\mathsf{C})}$$

Accuracy limited by measurement of  $C_T$  to  $\pm 0.1$  pF.

# MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115 TYPICAL DEVICE CHARACTERISTICS

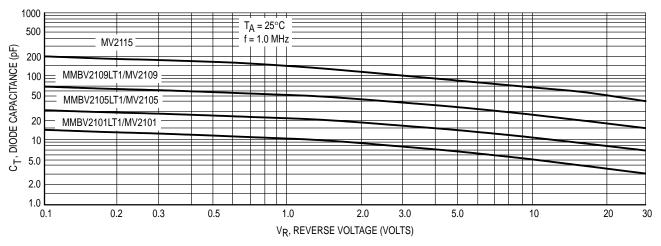


Figure 1. Diode Capacitance versus Reverse Voltage

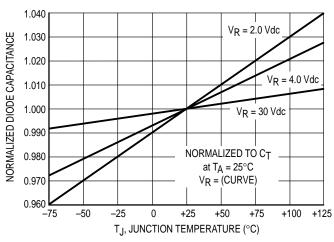


Figure 2. Normalized Diode Capacitance versus Junction Temperature

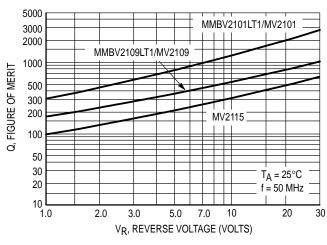


Figure 4. Figure of Merit versus Reverse Voltage

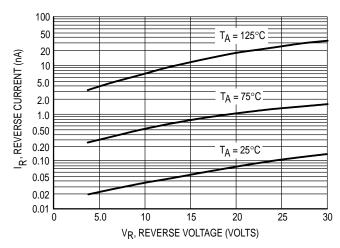


Figure 3. Reverse Current versus Reverse Bias Voltage

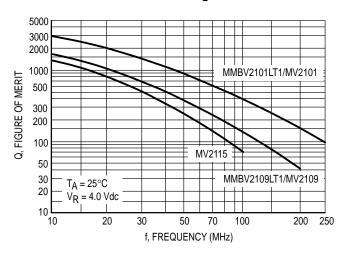
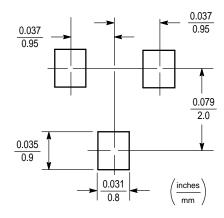


Figure 5. Figure of Merit versus Frequency

# MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115 MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-23

### POWER DISSIPATION FOR A SURFACE MOUNT DEVICE

The power dissipation for a surface mount device is a function of the pad size. These can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet,  $P_D$  can be calculated as follows.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T<sub>A</sub> of 25°C, one can calculate the power dissipation of the device. For example, for a SOT–23 device, P<sub>D</sub> is calculated as follows.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT–23 assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the surface mount packages. One is to increase the area of the drain/collector pad. By increasing the area of the drain/collector pad, the power dissipation can be increased. Although the power dissipation can almost be doubled with this method, area is taken up on the printed circuit board which can defeat the purpose of using surface mount technology.

Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

### **SOLDERING PRECAUTIONS**

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes.
   Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling
- \* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

# MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115 SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass

or stainless steel with a typical thickness of 0.008 inches. The stencil opening size for the surface mounted package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

### TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating "profile" for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 6 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time. The line on the graph shows the

actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

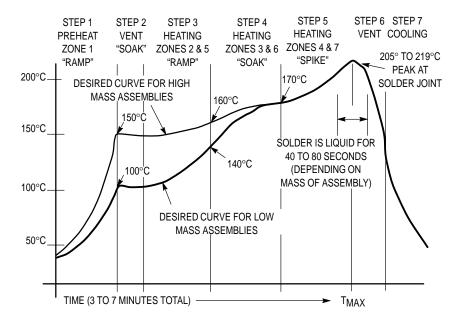
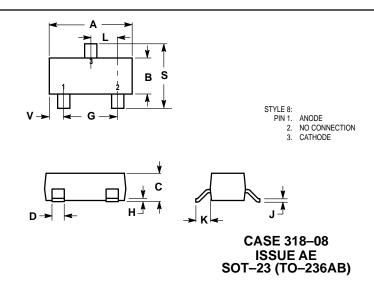


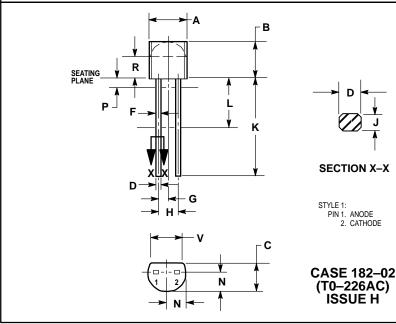
Figure 6. Typical Solder Heating Profile

### MMBV2101LT1 MMBV2103LT1 MMBV2105LT1 MMBV2107LT1 MMBV2108LT1 MMBV2109LT1 MV2101 MV2104 MV2105 MV2108 MV2109 MV2111 MV2115 PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

|     | INC      | HES    | MILLIMETERS |       |  |
|-----|----------|--------|-------------|-------|--|
| DIM | M MIN MA |        | MIN         | MAX   |  |
| Α   | 0.1102   | 0.1197 | 2.80        | 3.04  |  |
| В   | 0.0472   | 0.0551 | 1.20        | 1.40  |  |
| С   | 0.0350   | 0.0440 | 0.89        | 1.11  |  |
| D   | 0.0150   | 0.0200 | 0.37        | 0.50  |  |
| G   | 0.0701   | 0.0807 | 1.78        | 2.04  |  |
| Н   | 0.0005   | 0.0040 | 0.013       | 0.100 |  |
| J   | 0.0034   | 0.0070 | 0.085       | 0.177 |  |
| K   | 0.0180   | 0.0236 | 0.45        | 0.60  |  |
| L   | 0.0350   | 0.0401 | 0.89        | 1.02  |  |
| S   | 0.0830   | 0.0984 | 2.10        | 2.50  |  |
| ٧   | 0.0177   | 0.0236 | 0.45        | 0.60  |  |



### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH
- 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L.
   DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIM K MINIMUM.

|     | INC   | HES   | MILLIMETERS |       |  |
|-----|-------|-------|-------------|-------|--|
| DIM | MIN   | MAX   | MIN         | MAX   |  |
| Α   | 0.175 | 0.205 | 4.45        | 5.21  |  |
| В   | 0.170 | 0.210 | 4.32        | 5.33  |  |
| C   | 0.125 | 0.165 | 3.18        | 4.49  |  |
| ם   | 0.016 | 0.022 | 0.41        | 0.56  |  |
| F   | 0.016 | 0.019 | 0.407       | 0.482 |  |
| G   | 0.050 | BSC   | 1.27 BSC    |       |  |
| Η   | 0.100 | BSC   | 3.54 BSC    |       |  |
| 7   | 0.014 | 0.016 | 0.36        | 0.41  |  |
| K   | 0.500 | _     | 12.70       | _     |  |
| L   | 0.250 | _     | 6.35        |       |  |
| N   | 0.080 | 0.105 | 2.03 2.66   |       |  |
| Р   |       | 0.050 | 1.27        |       |  |
| R   | 0.115 |       | 2.93        |       |  |
| ٧   | 0.135 | _     | 3.43        |       |  |

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 $\Diamond$ MMBV2101LT1/D